

PUMD6-Q

50 V, 100 mA NPN/PNP Resistor-Equipped Transistor; R1 = 4.7 k Ω , R2 = open

4 January 2024

Product data sheet

1. General description

NPN/PNP Resistor-Equipped Transistor (RET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- · Built-in bias resistors
- Simplifies circuit design
- · Reduces component count
- Reduces pick and place costs
- Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

- · Digital application in industrial segments
- Switching loads
- · Low current peripheral driver
- Controlling IC inputs
- Cost-saving alternative to BC847 / BC857 series in digital applications

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
V _{CEO}	collector-emitter voltage	open base	[1]	-	-	50	V
Io	output current		[1]	-	-	100	mA
R1	bias resistor 1 (input)	T _{amb} = 25 °C	[2]	3.3	4.7	6.1	kΩ

- [1] For the PNP transistor with negative polarity.
- [2] See section "Test information" for resistor calculation and test conditions.



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1		O1 I2 GND2
2	l1	input (base) TR1	□6 □5 □4	
3	O2	output (collector) TR2		R1 R
4	GND2	GND (emitter) TR2		TR1
5	12	input (base) TR2	H ₁ H ₂ H ₃	R1
6	O1	output (collector) TR1	TSSOP6 (SOT363)	GND1 I1 O2 006aaa269

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PUMD6-Q		plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	<u>SOT363</u>		

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PUMD6-Q	D%6

[1] % = placeholder for manufacturing site code

50 V, 100 mA NPN/PNP Resistor-Equipped Transistor; R1 = 4.7 kΩ, R2 = open

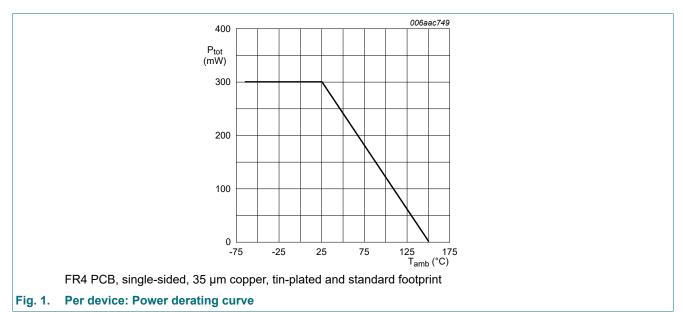
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transisto	or					
V _{CBO}	collector-base voltage	open emitter	[1]	-	50	V
V_{CEO}	collector-emitter voltage	open base	[1]	-	50	V
V_{EBO}	emitter-base voltage	open collector	[1]	-	5	V
VI	input voltage	TR1 (NPN)		-5	30	V
		TR2 (PNP)		-30	5	V
Io	output current		[1]	-	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[2]	-	200	mW
Per device				'		
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[2]	-	300	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] For the PNP transistor with negative polarity.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided, 35 µm copper, tin-plated and standard footprint.



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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor	er transistor						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	625	K/W
Per device	Per device						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	416	K/W

[1] Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint.

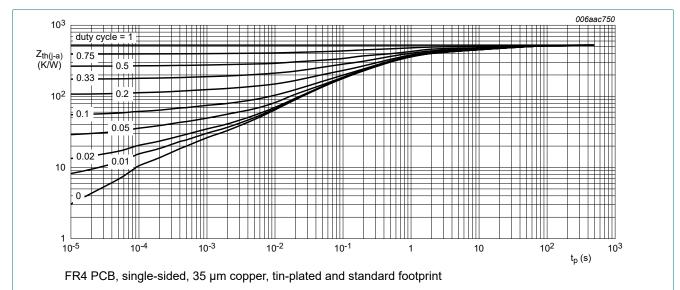


Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

50 V, 100 mA NPN/PNP Resistor-Equipped Transistor; R1 = 4.7 k Ω , R2 = open

10. Characteristics

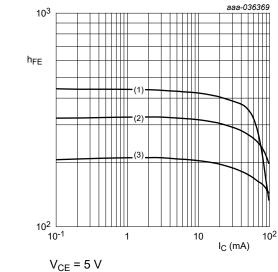
Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	tor						
V _{(BR)CBO}	collector-base breakdown voltage	$I_C = 100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$	[1]	50	-	-	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	$I_C = 2 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$	[1]	50	-	-	V
I _{CBO}	collector-base cut-off current	V _{CB} = 50 V; I _E = 0 A; T _{amb} = 25 °C	[1]	-	-	100	nA
I _{CEO}	collector-emitter cut-off	V _{CE} = 30 V; I _B = 0 A; T _{amb} = 25 °C	[1]	-	-	100	nA
	current	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}; T_{j} = 150 ^{\circ}\text{C}$	[1]	-	-	5	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	[1]	-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 1 mA; T _{amb} = 25 °C	[1]	200	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 5 \text{ mA}; I_B = 0.25 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	[1]	-	-	100	mV
$V_{I(off)}$	off-state input voltage	V _{CE} = 5 V; I _C = 100 μA; T _{amb} = 25 °C	[1]	-	585	500	mV
V _{I(on)}	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 10 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	[1]	1.3	0.88	-	V
R1	bias resistor 1 (input)	T _{amb} = 25 °C	[2]	3.3	4.7	6.1	kΩ
TR1 (NPN)	·						·
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; $ $T_{amb} = 25 \text{ °C}$		-	-	2.5	pF
f _T	transition frequency	V_{CE} = 5 V; I_{C} = 10 mA; f = 100 MHz; T_{amb} = 25 °C	[3]	-	230	-	MHz
TR2 (PNP)	'						
C _c	collector capacitance	V_{CB} = -10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C		-	-	3	pF
f _T	transition frequency	V_{CE} = -5 V; I_{C} = -10 mA; f = 100 MHz; T_{amb} = 25 °C	[3]	-	180	-	MHz

For the PNP transistor with negative polarity.
See section "Test information" for resistor calculation and test conditions. [2] [3]

Characteristics of built-in transistor

50 V, 100 mA NPN/PNP Resistor-Equipped Transistor; R1 = 4.7 k Ω , R2 = open



 $(1) T_{amb} = 100 °C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -40 \, ^{\circ}C$

TR1 (NPN): DC current gain as a function of Fig. 3. collector current; typical values

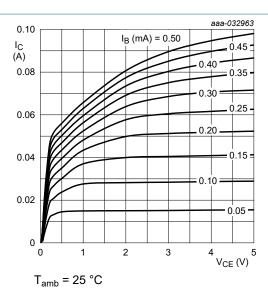
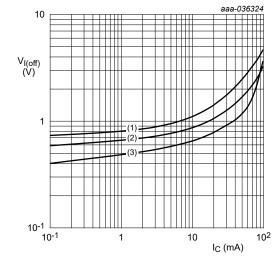


Fig. 4. TR1 (NPN): Collector current as a function of collector-emitter voltage; typical values



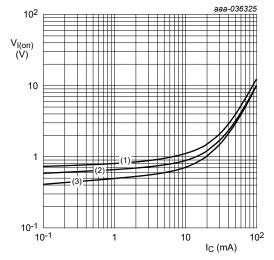
 $V_{CE} = 5 V$

(1) $T_{amb} = -40 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

TR1 (NPN): Off-state input voltage as a function | Fig. 6. Fig. 5. of collector current; typical values



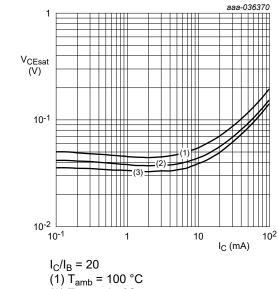
 $V_{CE} = 0.3 V$

(1) T_{amb} = - 40 °C (2) T_{amb} = 25 °C

(3) $T_{amb} = 100 \, ^{\circ}C$

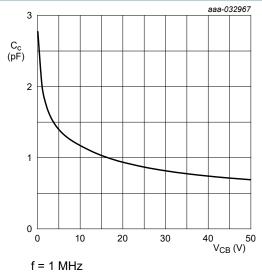
TR1 (NPN): On-state input voltage as a function of collector current; typical values

50 V, 100 mA NPN/PNP Resistor-Equipped Transistor; R1 = 4.7 k Ω , R2 = open



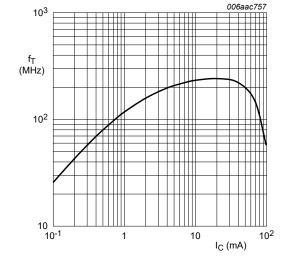
(2) $T_{amb} = 25 \,^{\circ}\text{C}$ (3) $T_{amb} = -40 \,^{\circ}\text{C}$

Fig. 7. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$

Fig. 8. TR1 (NPN): Collector capacitance as a function of collector-base voltage; typical values

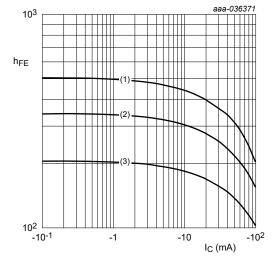


f = 100 MHz

T_{amb} = 25 °C

 $V_{CE} = 5 V$

TR1 (NPN): Transition frequency as a function Fig. 9. of collector current; typical values of built-in transistor



 $V_{CE} = -5 V$

(1) T_{amb} = 100 °C (2) T_{amb} = 25 °C

(3) $T_{amb} = -40 \, ^{\circ}C$

Fig. 10. TR2 (PNP): DC current gain as a function of collector current; typical values

50 V, 100 mA NPN/PNP Resistor-Equipped Transistor; R1 = 4.7 k Ω , R2 = open

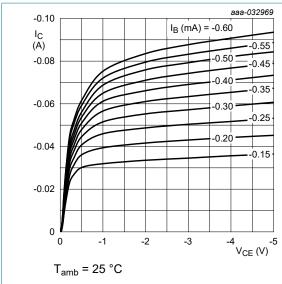
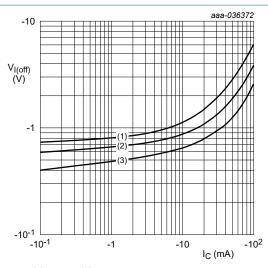


Fig. 11. TR2 (PNP): Collector current as a function of collector-emitter voltage; typical values



$$V_{CE} = -5 V$$

(1) $T_{amb} = -40 ^{\circ}C$
(2) $T_{amb} = 25 ^{\circ}C$
(3) $T_{amb} = 100 ^{\circ}C$

Fig. 12. TR2 (PNP): Off-state input voltage as a function of collector current; typical values

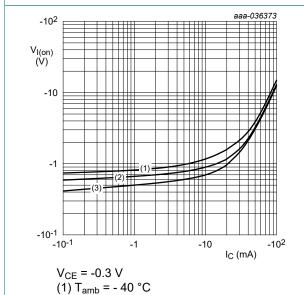
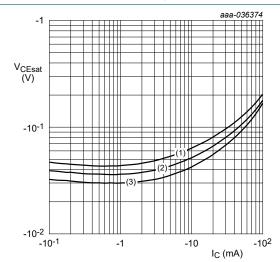


Fig. 13. TR2 (PNP): On-state input voltage as a function | Fig. 14. TR2 (PNP): Collector-emitter saturation voltage of collector current; typical values

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$



 $I_{\rm C}/I_{\rm B} = 20$ (1) $T_{amb} = 100 \, ^{\circ}C$ $(2) T_{amb} = 25 °C$ (3) $T_{amb} = -40 \, ^{\circ}C$

as a function of collector current; typical values

50 V, 100 mA NPN/PNP Resistor-Equipped Transistor; R1 = 4.7 k Ω , R2 = open

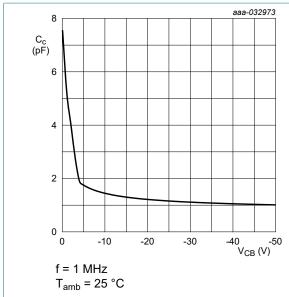


Fig. 15. TR2 (PNP): Collector capacitance as a function of collector-base voltage; typical values

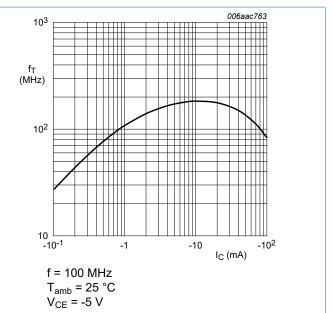


Fig. 16. TR2 (PNP): Transition frequency as a function of collector current; typical values of built-in transistor

50 V, 100 mA NPN/PNP Resistor-Equipped Transistor; R1 = 4.7 k Ω , R2 = open

11. Test information

Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

Resistor calculation

Calculation of bias resistor 1 (R1)

$$R_{I} = \frac{V(I_{2}) - V(I_{I})}{I_{2} - I_{I}}$$

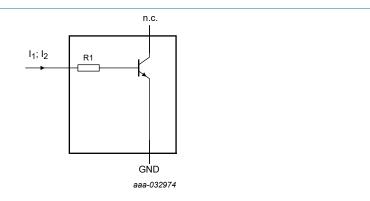


Fig. 17. TR1 (NPN): Resistor test circuit

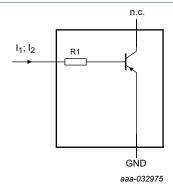


Fig. 18. TR2 (PNP): Resistor test circuit

Resistor test conditions

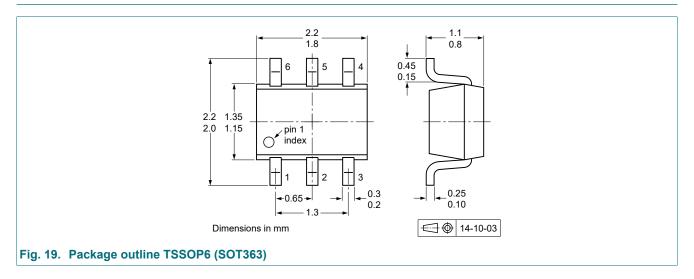
Table 8. Resistor test conditions

PUMD6	R1 (kΩ)	R2 (kΩ)	Test conditions		
			I ₁	l ₂	
TR1 (NPN)	4.7	open	600 μΑ	700 μΑ	
TR2 (PNP)	4.7	open	-600 μΑ	-700 μA	

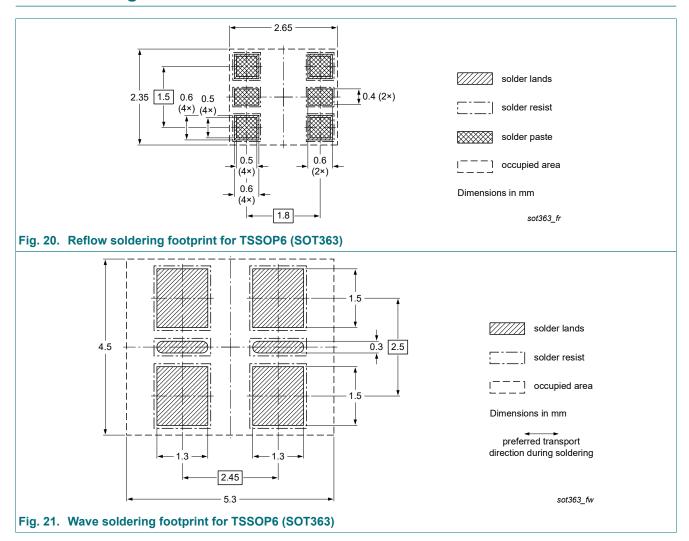
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12. Package outline



13. Soldering



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14. Revision history

Table 9. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PUMD6-Q v.1	20240104	Product data sheet	-	-

50 V, 100 mA NPN/PNP Resistor-Equipped Transistor; R1 = 4.7 k Ω , R2 = open

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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